



Advances in pixel electronics for experiments with high rate and radiation

M. Garcia-Sciveres
Lawrence Berkeley National Lab

Hiroshima Conference
Okinawa, Dec. 13, 2017



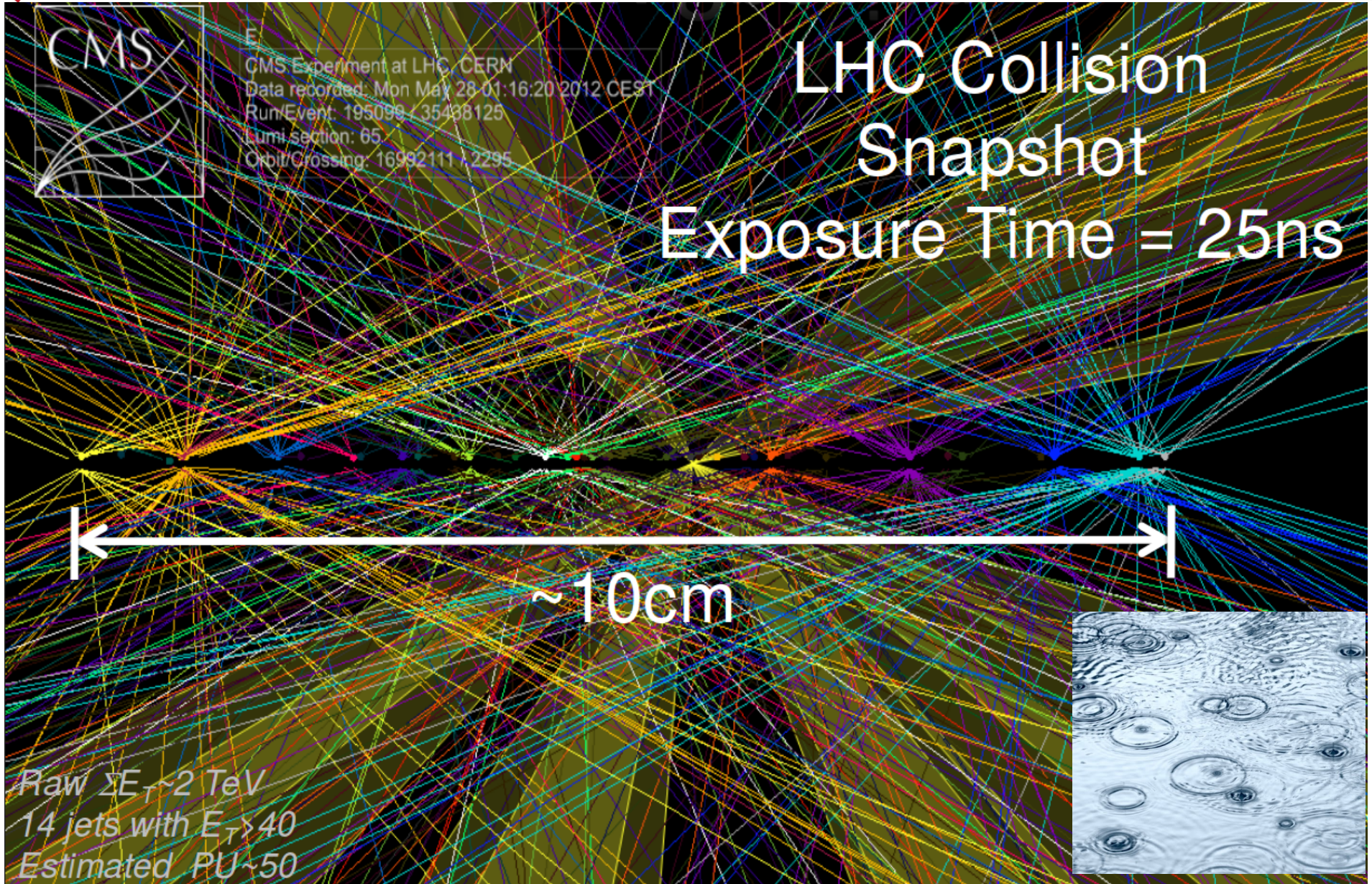
Introduction



- “Pre”cedings: arxiv 1705.10150
- Several topics covered in N. Wermes: “Pixel Detector Overview”
- Other topics have dedicated talks/posters – will point out
- Will focus this talk on readout chip developments:
 - High rate and small feature size
 - Total dose radiation tolerance and small feature size
 - Power delivery
 - Data transmission
 - Control and operation considerations, including SEU
 - Practical IC design model
 - Outlook: what needs rethinking?



Obligatory Pileup Slide





Rate

Particles / Hits

LHC



HL-LHC



- * Store full time sequence of drops until trigger (not collect in a bucket)
- * Can quantify rate as memory bits / area / time
(note: no mention of pixel size)

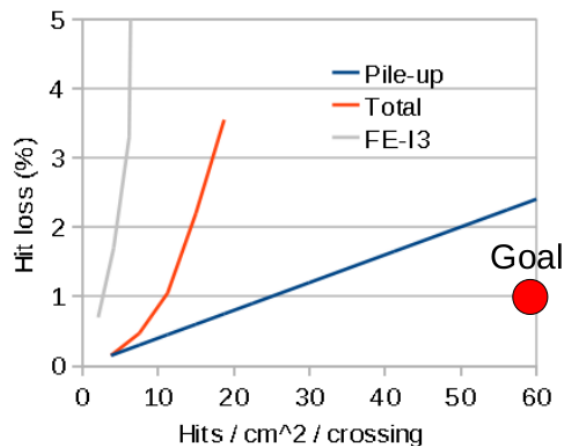
Getting to Higher Logic Density



From Hiroshima 09

Future Directions

- Still higher rate capability
- Need smaller, faster pixel
- Yet need more memory per pixel to buffer higher rate
- Two directions to explore: 3D and 65nm
 - FE-I4 region placed on 2 130nm tiers would have 60% pixel size and 50% more logic/memory



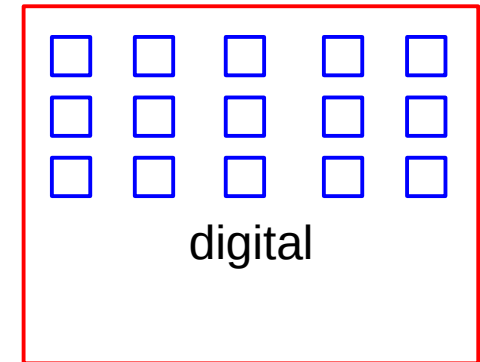
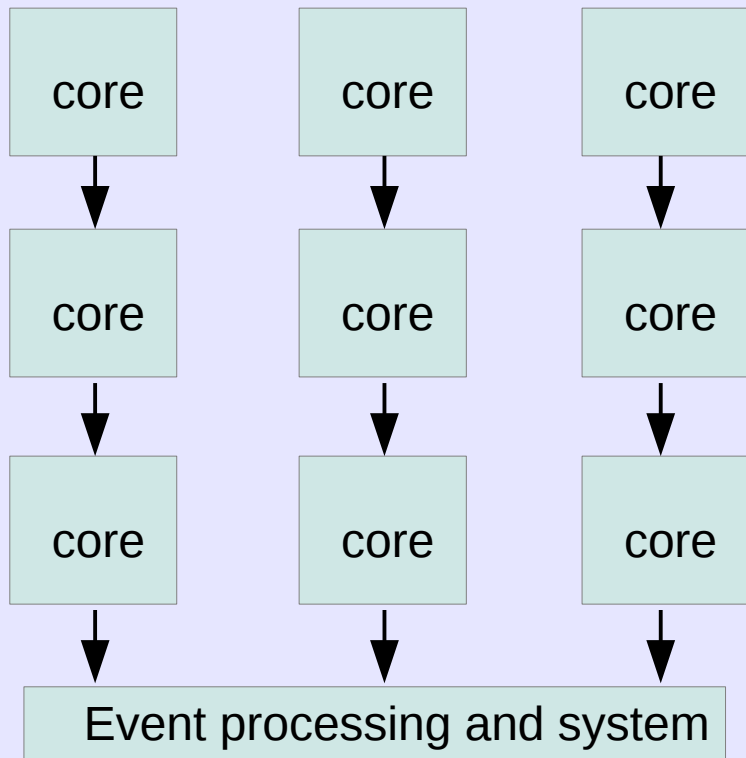
FE-I3 pixel -- 3.2 bits

FE-I4 -- 25 bits

~35 bits

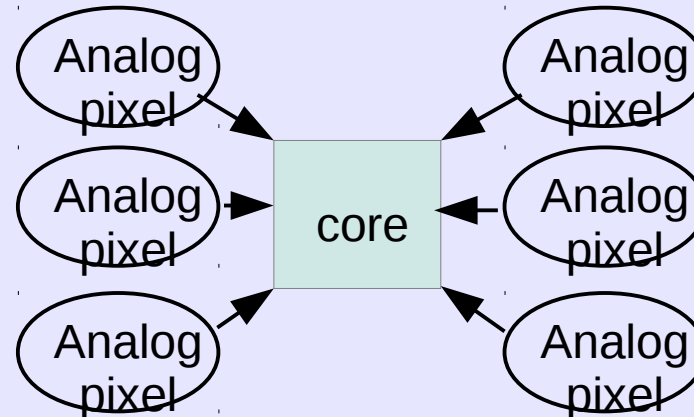


Chip Concept from Pixel 2012



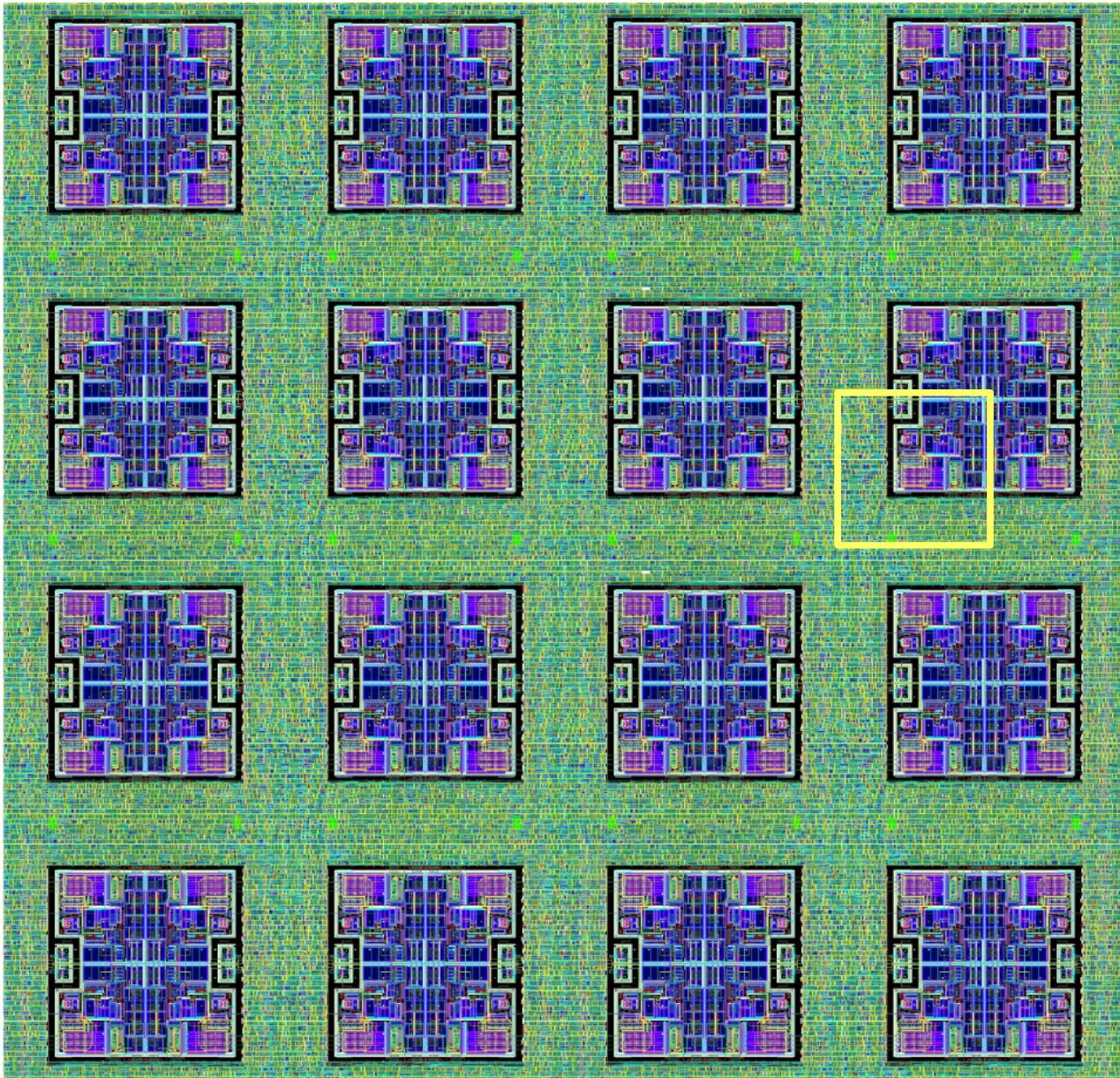
(looks more like commercial chip)

HL-LHC





One RD53A Chip Core



One flat synthesized circuit
Each pixel is different !

Whole block is stepped
and repeated

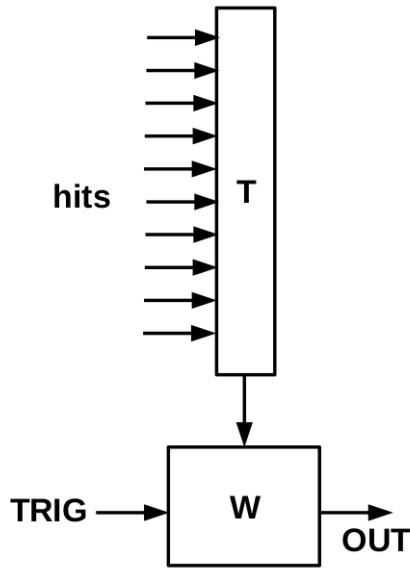
~ 200k transistors
Size chosen so it CAN
be SPICE simulated

(routing dominated re: metal stack)



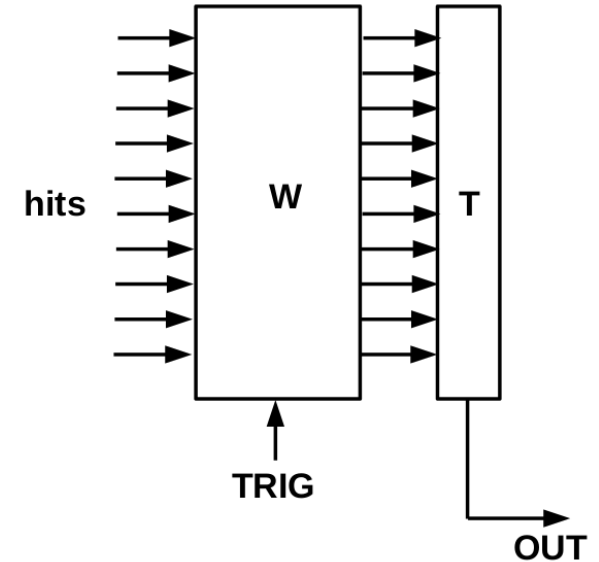
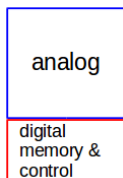
Hit Storage Architectures

T=Transfer W=Wait



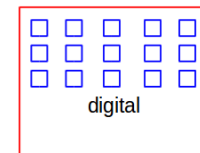
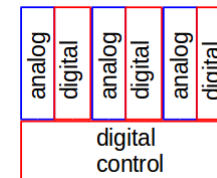
Move all hits immediately to a big common buffer. Wait for trigger there.

W="End of Column Buffer"



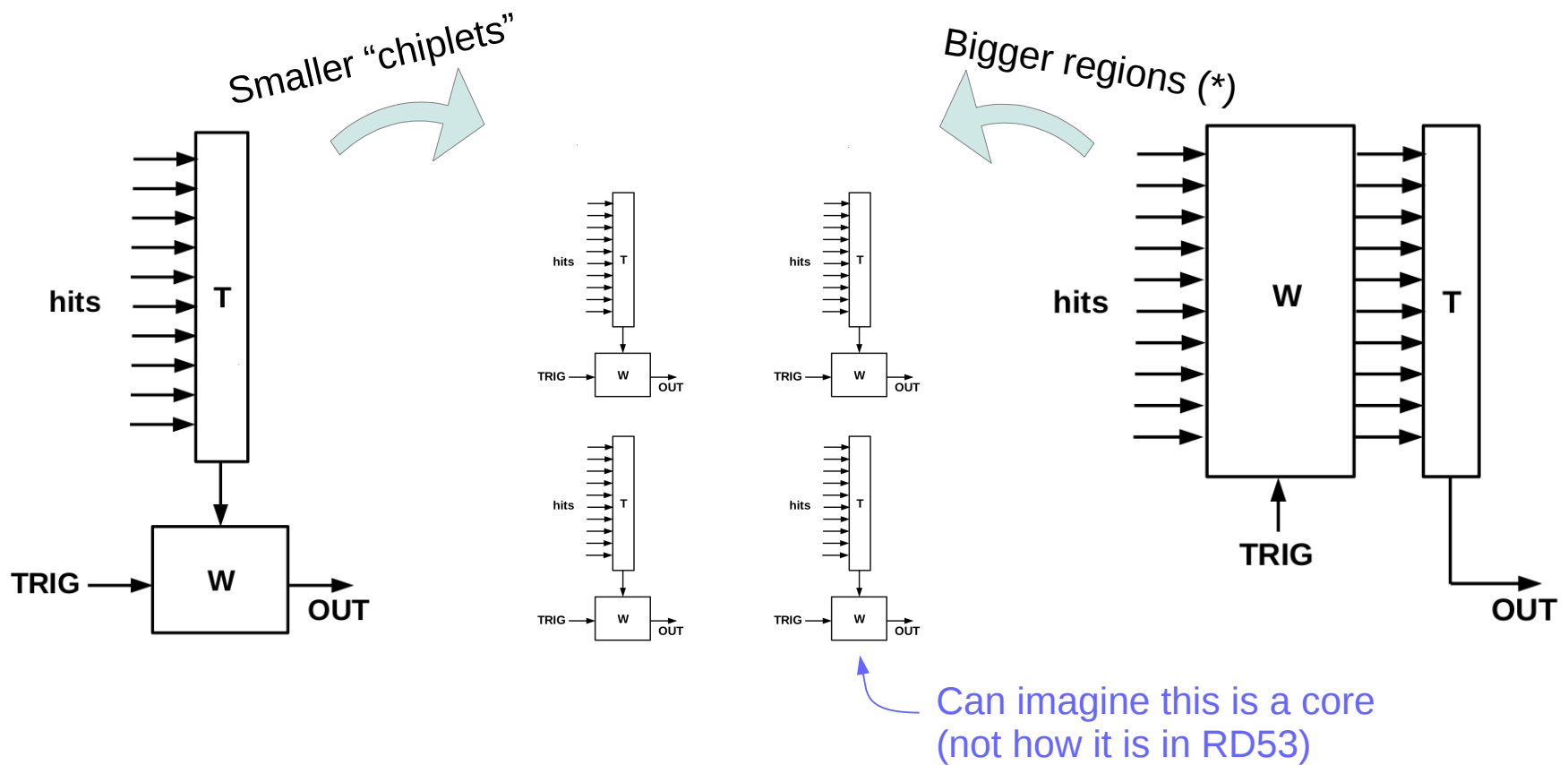
Keep hits in a local buffer. Transfer only those triggered.

W="Region"





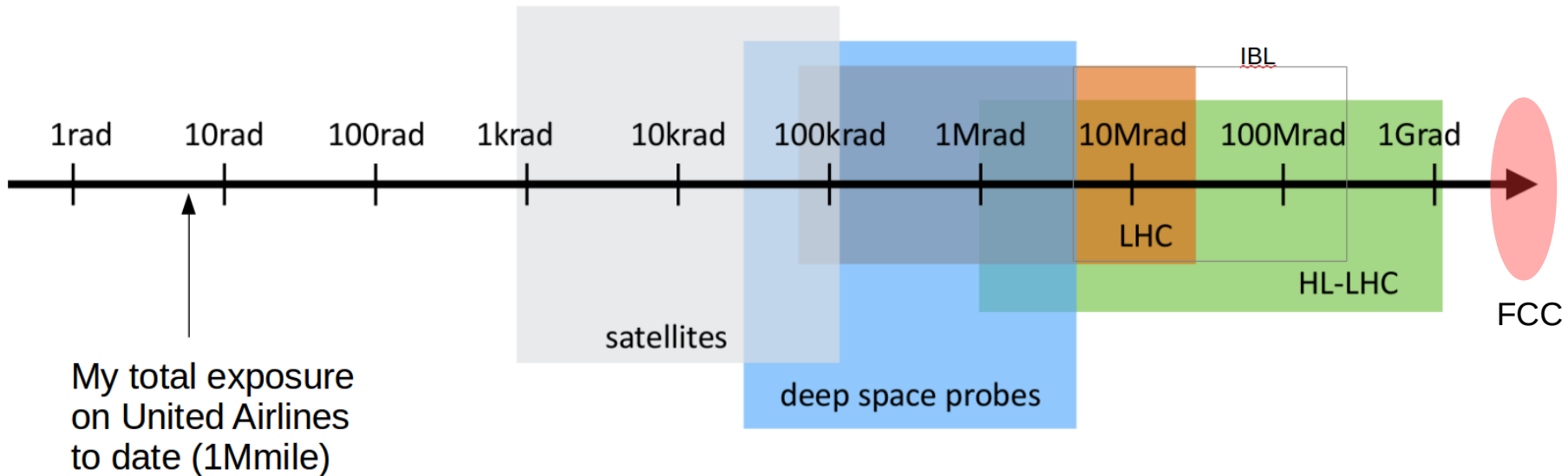
Hit Storage Architectures 2



- Really two extremes of the same problem
- (*) See poster "A Novel Pixel Region Architecture for Pixel detector at HL-LHC..."



Radiation



F. Faccio: CMOS technologies and power distribution components for HL-LHC: radiation strikes back
Wednesday, 13 December 2017 09:00 (30)

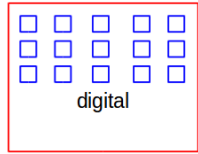
Will only talk about how radiation effects have been taken into account in this talk



Rad Hard Logic Density Scaling



28nm ?



65nm

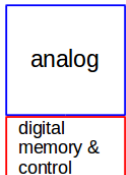
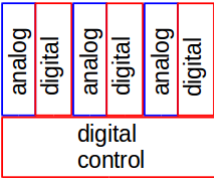
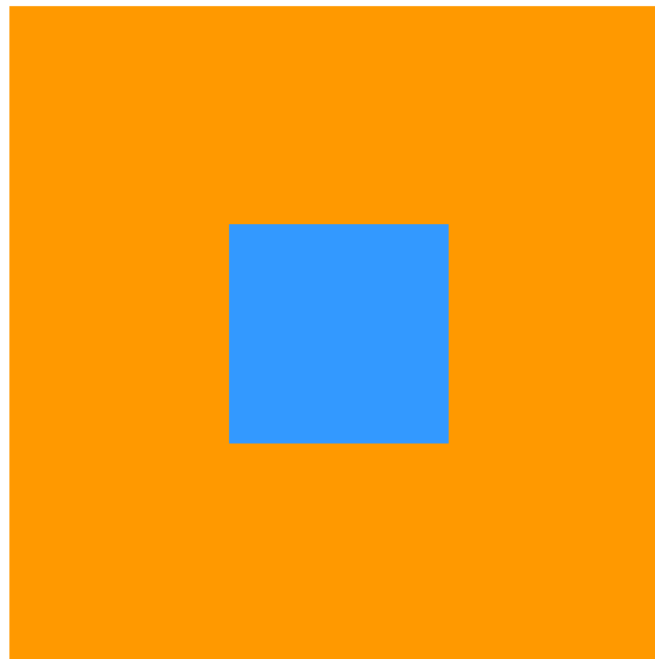


Not quite min. size due to pesky radiation damage.
But still 2-3x higher logic density than 130nm.

130nm



0.25um
ELT





Temperature, Time, Dose rate, Process



- There are many dimensions to the radiation damage problem
- They all have to be taken into account
- But if you do, you can make a pixel chip that works up to 1Grad
- Analog circuits no problem. Several test chips irradiated this high and work fine
- Digital (small transistors)
- Operate cold and don't heat it up under power (just like sensors!),
- Low dose rate caveat (see tomorrow's talk)
- We will soon have RD53A chips working after 1Grad
- We only guaranteed specs up to 500Mrad, because that's what we could simulate, and this was using pessimistic models.
- Radiation damage simulation in the digital design process is now a necessity. Development of more accurate models is an ongoing process.

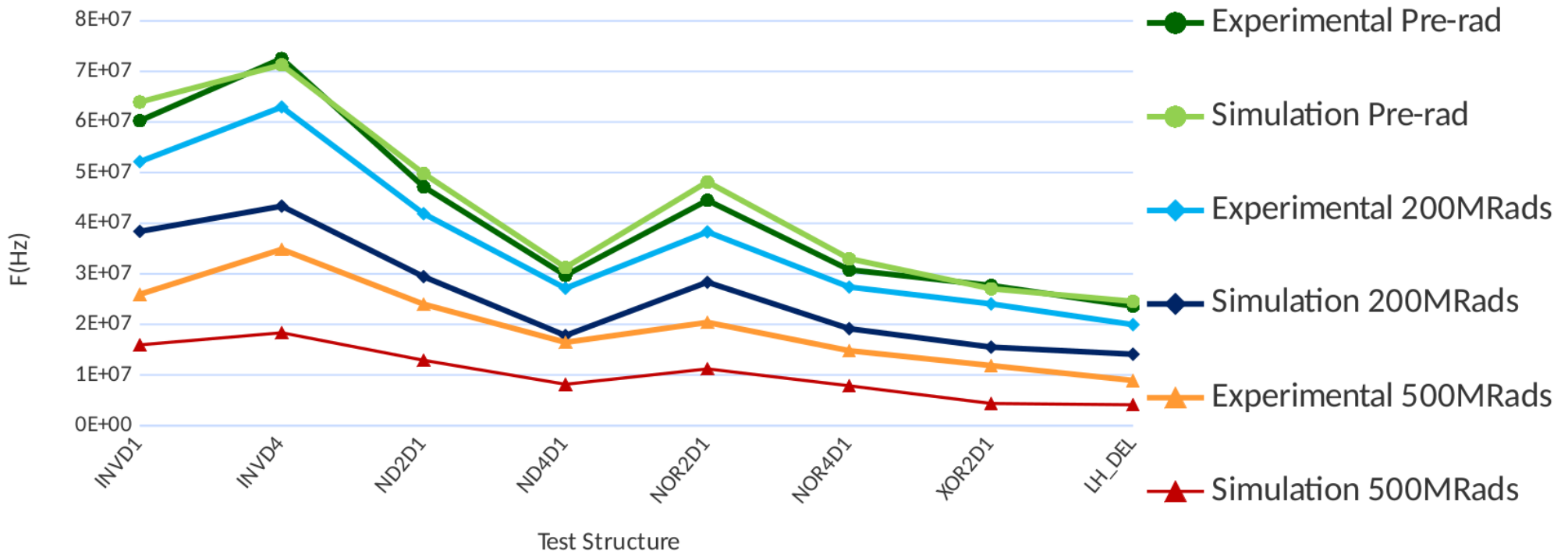


Data-Simulation Comparison



- Comparison of models used in RD53A chip with test chip data.
- Ring oscillator frequency is sensitive to TID effects
- Different logic cells can be used to make ring oscillator test structures
- Models were built from single transistor data under DC worst case bias.
- A switching transistor is less vulnerable. We see 2x less damage.

Ring Oscillator frequencies 9T_NVT





Power distribution



- On-module power conversion needed as detectors get larger
- But not yet used in any running detector
- Will be a feature in HL-LHC ATLAS and CMS trackers

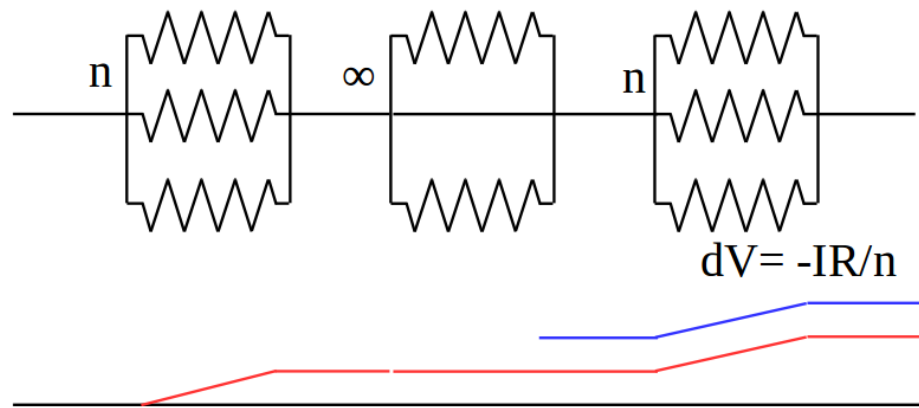
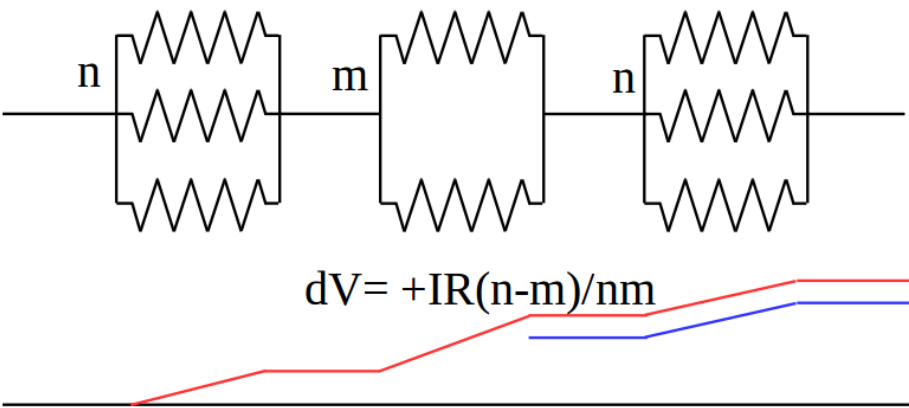
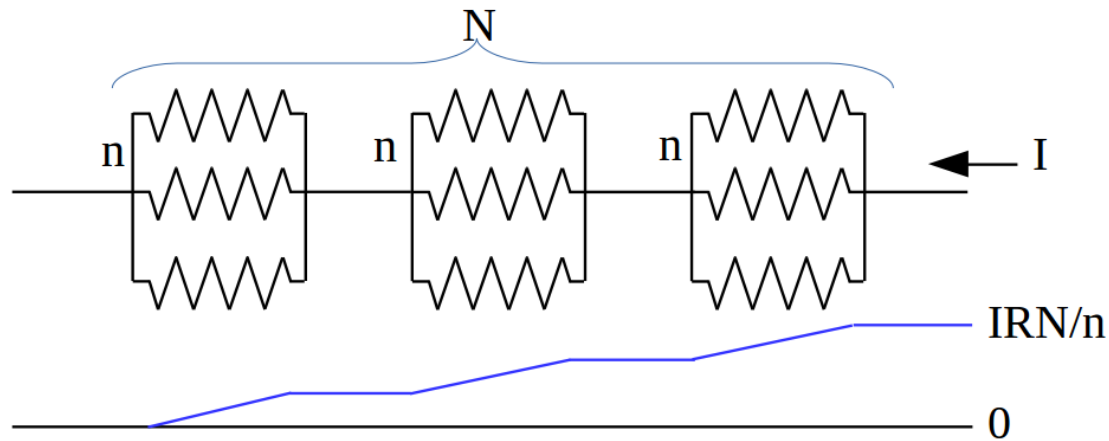
- In the case of pixels this will be done with serial power
- In-chip DC-DC was the alternative- but was not developed to maturity
- Off-chip DC-DC not suitable for pixel modules: too massive

- Successful demonstrations of serial power since many years
- Will not review. Will show the scheme adopted by RD53



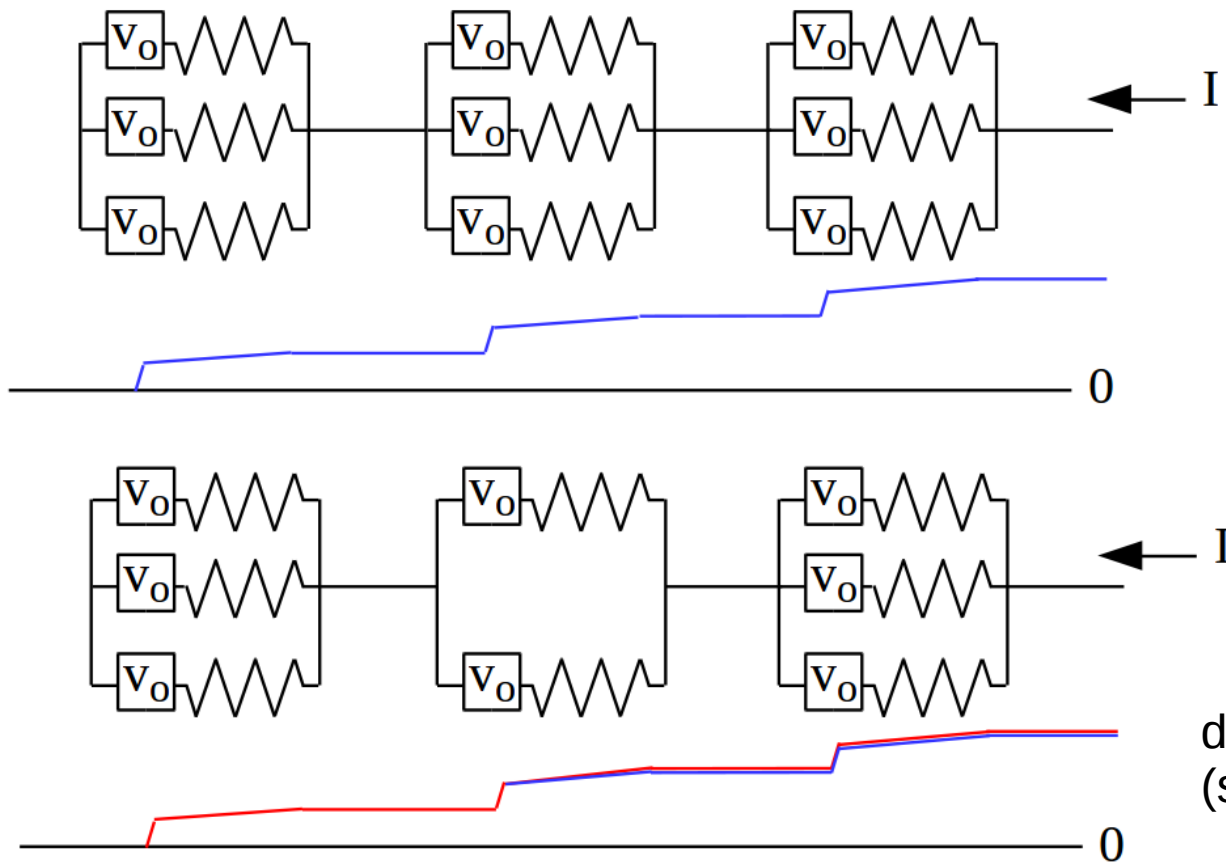
Resistive Serial Chain 101

- Should $R = V_{chip}/I_{chip}$?
- Narrow operating current range
- Significant power overhead
- Low open-fault tolerance
- V transients can be dangerous





Zenner-like using V-offset



$R \ll V_{chip}/I_{chip}$

Wide operating current range

Reduced power overhead

Tolerates multiple faults per module

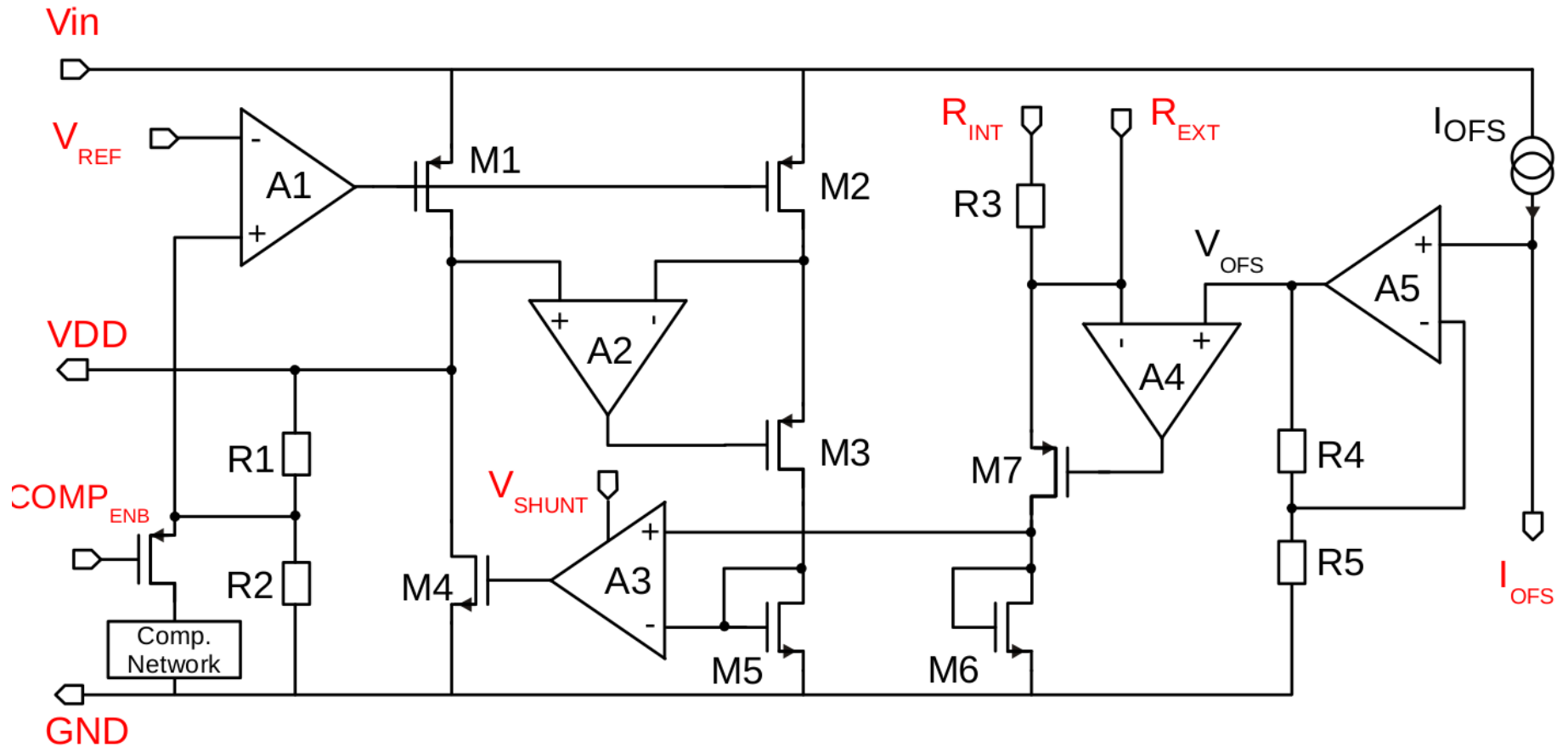
V_0 matching important

No different for shorted module

$dV \ll \text{module } V$
(same formula, smaller R)



RD53A chip regulator schematic





Data Transmission



- On-module power conversion reduces the power cable plant
- At the same time, output bandwidth goes up a lot (pileup x trigger rate)
 - ATLAS IBL chip output = 160 Mbps
 - HL-LHC ATLAS/CMS inner layer chip output = 5.12 Gbps
- Direct chip to optical fiber, Grad rad hard, low power, miniature technology not available
- Data cables become the dominant services mass problem
- Solution: fit as much data as possible onto low mass cables
- Many complications to be overcome
- A very active development area
- Industry very far ahead- learning and catching up to be done



Data Transmission Problems/R&D Areas

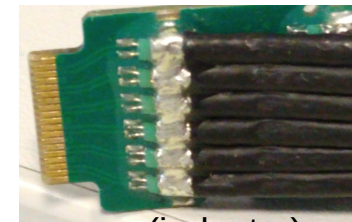


- Low mass, high bandwidth cables and connectors

- Many options at 1Gbps for length ~1m.
- Few options for 5Gbps for length 1-5m.



Our twinax



theirs

(industry)

- Reliable recovery of signals from lossy transmission lines

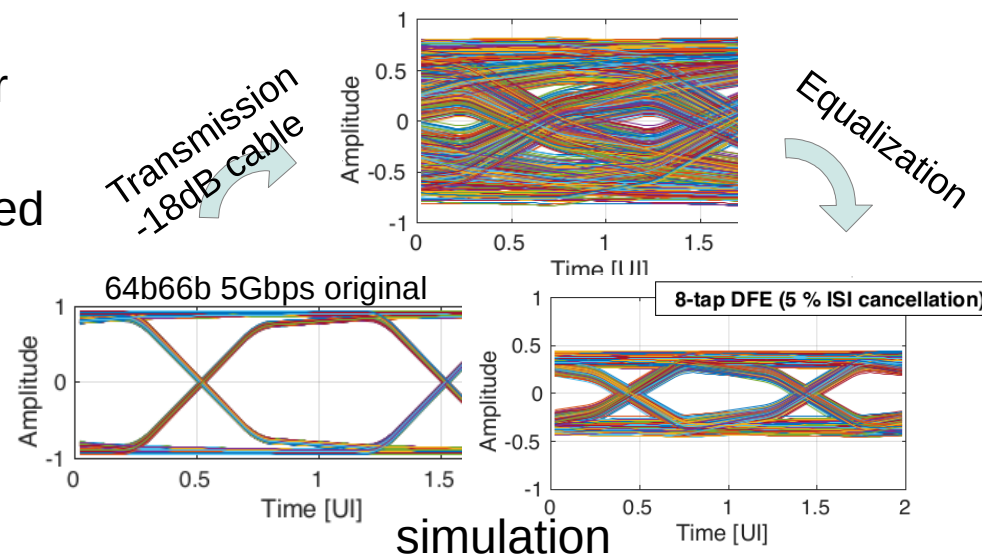
- Pre-emphasis and equalization
- Transmitters on modern FPGA can recover signals after -28dB loss.
- With radiation, less advanced circuits, added clock jitter, etc, it will be challenging for us to achieve recovery after -20dB loss.

- High speed serialization on chip

- next slide

- Data encoding and data compression

- 8b/10b was considered pretty advanced for HEP a few years ago
- RD53A has multi-lane 64b/66b output
- Multi-level, PAM-4, PAM-16 not yet explored
- Compression algorithms such as Huffman being explored by not yet used





High Speed Serialization on Chip



- Need a high quality clock (<15ps jitter for 5 Gbps, <75ps for 1 Gbps)
 - Problem: no high quality, high speed clock coming in
 - Adding one means adding mass
 - PLL multiplication used, but hard to achieve very low jitter, especially after radiation
- Need a high speed serializer that remains high speed after radiation damage
- Need fast recovery from SEU
- 1 Gbps seems achievable after irradiation, 5 Gbps still a challenge
- This means HL-LHC inner layer chips must have 4 output lanes
- LHCb Velopix uses 4x 5Gbps lanes, but less radiation, good incoming clock, and high quality output cables.
- LpGBT can run at 10Gbps, but high speed low jitter incoming reference signal, and less radiation.



Control



- Take advantage of high logic density to implement smarter control functions
- Chip becomes fairly intelligent and “user friendly” to control
- Learn from present operational issues and design a control protocol where they do not arise
 - See earlier ATLAS and CMS pixel operation talks
- In general, SEU’s cause all kinds of exceptions that the DAQ protocol does not easily recover from.
 - Will never manage to prevent SEU- it will only get worse in the future
 - Solution: design protocols that are compatible with SEU’s
 - No long-term memory in the chip: refresh configuration all the time from outside during data taking
 - “Trickle configuration” already supported in RD53A
 - Make no use of counter absolute values- only differences matter so upsets fix themselves when counters loop.
 - “Tagged trigger” protocol already supported in RD53A

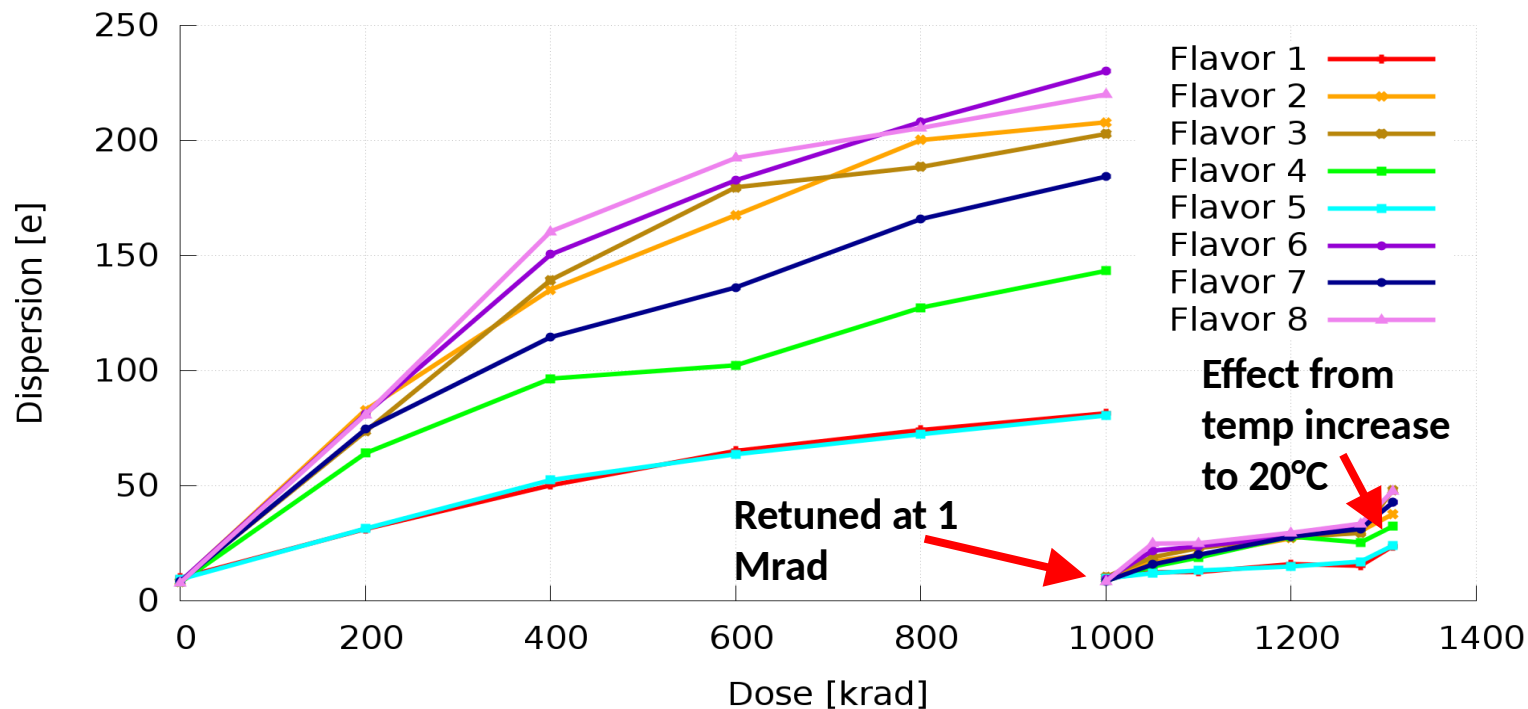


New concerns: Low dose rate is not so low

1 Mrad per run at HL-LHC ! But dose rate here was ~5x higher than at HL-LHC

Threshold Dispersion vs. Dose

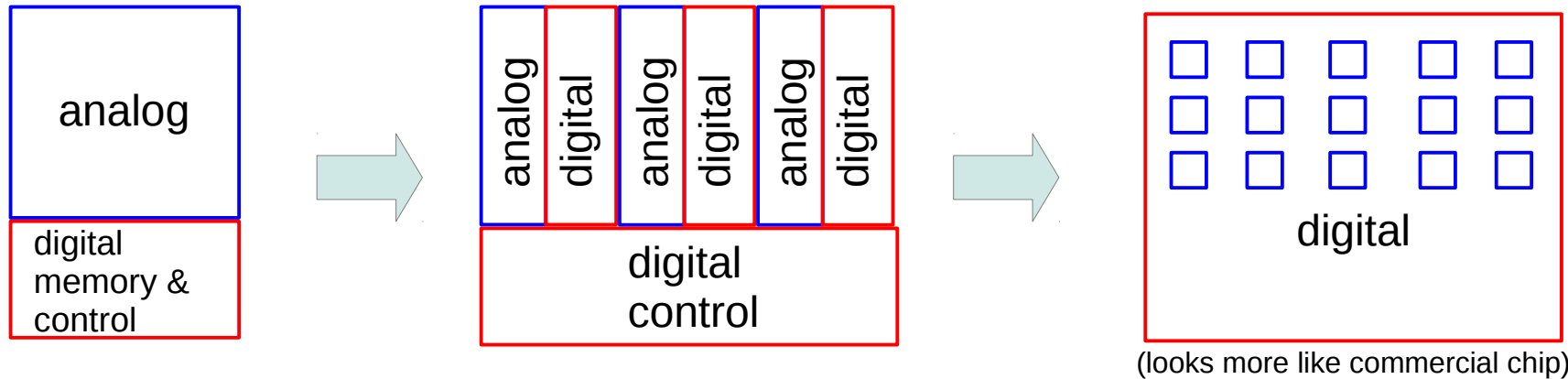
Column Flavor Dispersion - 88" Irradiation



Automated, continual threshold self-tuning would address this



Shift in Design Approach



Single institute team

FE-I4

Participating institutes:

[Bonn](#): D. Arutinov, M. Barbero, T. Hemperek, A. Kruth, M. Karagounis.

[CPPM](#): D. Fougeron, M. Menouni.

[Genova](#): R. Beccherle, G. Darbo.

[LBNL](#): S. Dube, D. Elledge, M. Garcia-Sciveres, D. Gnani, A. Mekkaoui.

[Nikhef](#): V. Gromov, R. Kluit, J.D. Schipper



Nov. 2017 RD53 meeting, CERN

Commercial style design and validation
10⁹ transistor Chips work the first time



Where next?



Still a couple of years to go for RD53 to make production chips for ATLAS & CMS

And after that?

- Higher logic density (28nm)
- Higher radiation dose
- Smaller pixels
- More functionality



- R&D into smaller features
- Followed by another collaboration to make next gen. chip

What for?

Replacement of HL-LHC inner layers, FCC



Smaller pixels and resolution



- Refer back to W. Snoey's talk...
- Single pixel gets "easier" due to smaller capacitance (eg. no timewalk)
- But total power budget gets more challenging (capacitance per unit area goes up- scales with perimeter, not area)
- At what point should we go binary?
 - See poster: "Ultimate position resolution of pixel clusters with binary readout..."
- High bandwidth data transmission. Data compression.



Conclusions



- High rate (*) needs high logic density (hybrid > monolithic forever)
- Digital design flow and tools needed to make 10^9 transistor chips that work the first time
- Design collaboration model probably here to stay
- High radiation needs high radiation tolerance-
 - Some tension with high density- see F. Faccio's talk
- High logic density comes with huge functionality potential- have to keep thinking of what to do with it
- (*) readout bandwidth limited. Will likely stay that way